IEEE SW Test Workshop Semiconductor Wafer Test Workshop

January Kister
Stephen Hopkins
MicroProbe, Inc.



MicroProbe Vx-MP Probe Card Technology



June 8-11, 2008 San Diego, CA USA

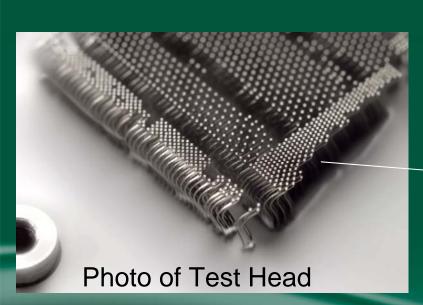
Overview

- Vx-MP Technology Key Features and Components
- Probe Design Considerations
- Key Performance Parameters
- Probe to Probe No-interference
 Confidence at Aggressive Bump Pitches
- Roadmaps
- Summary



Vx-MP Technology Key Features

Combines Flexibility of MEMS probes installed in customer-specified x-y locations







9229

Vx-MP Technology Key Features

 Probes are fabricated utilizing 3-D photolithography-metal plating techniques

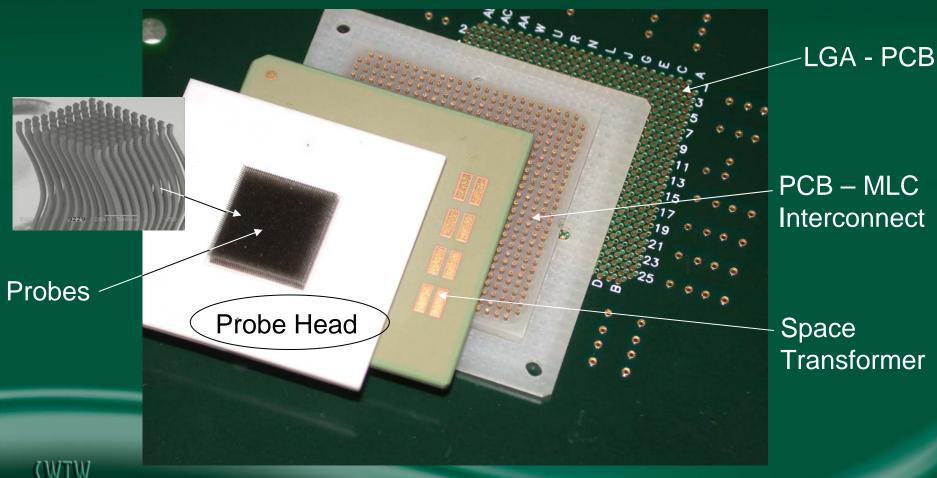
Probe tip – "skate" shape/material provides

ideal contactor

Probe body material provides optimal spring action



Vx-MP Technology Key Components

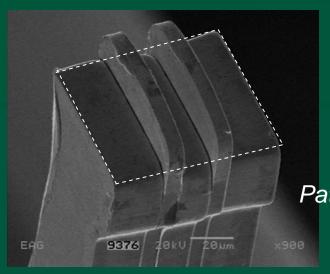




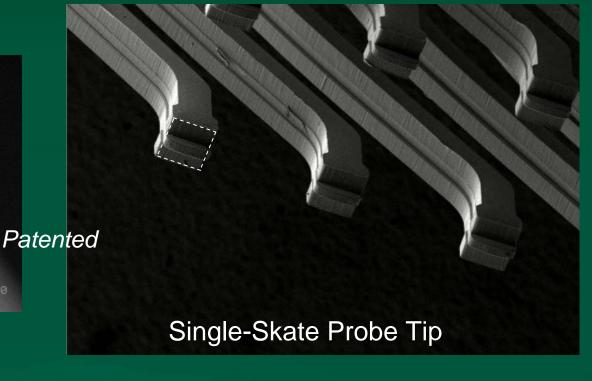
Vx-MP Probe Design Key **Features**

Tip base provides stable target for prober

alignment



Dual-Skate Probe Tip

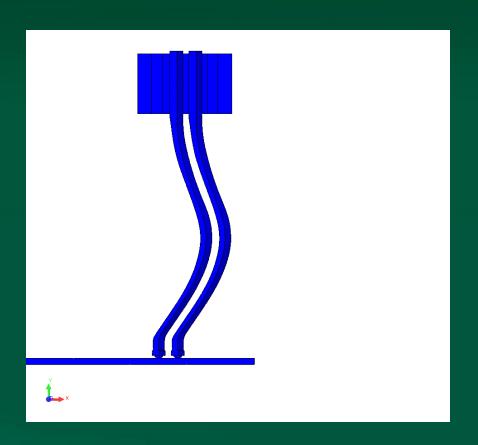




Tip Base (flat)

Vx-MP Key Performance Features

Vx-MP Probe Action

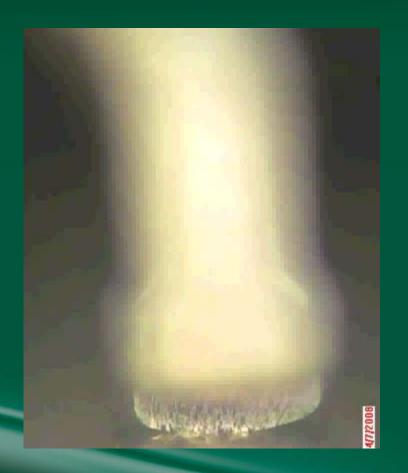




Patented

Vx-MP Mechanical Performance

Vx-MP Probe Scrub Motion



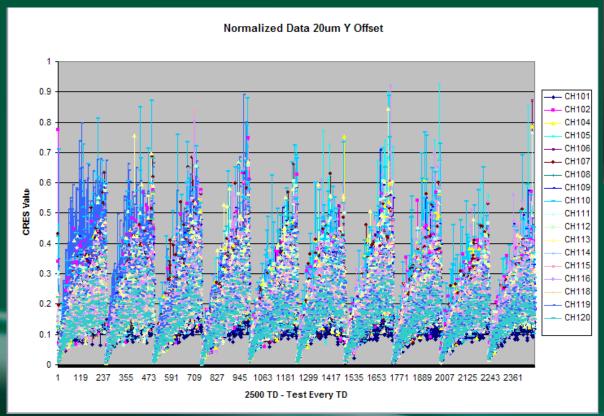
Patented



 Performance on Eutectic Flip-Chip Solder Balls, 400mA current prior to each measurement, 50 um Deflection

2500 TD, On-line clean cycle every 250 TD

Contact Resistance Change, Ohr

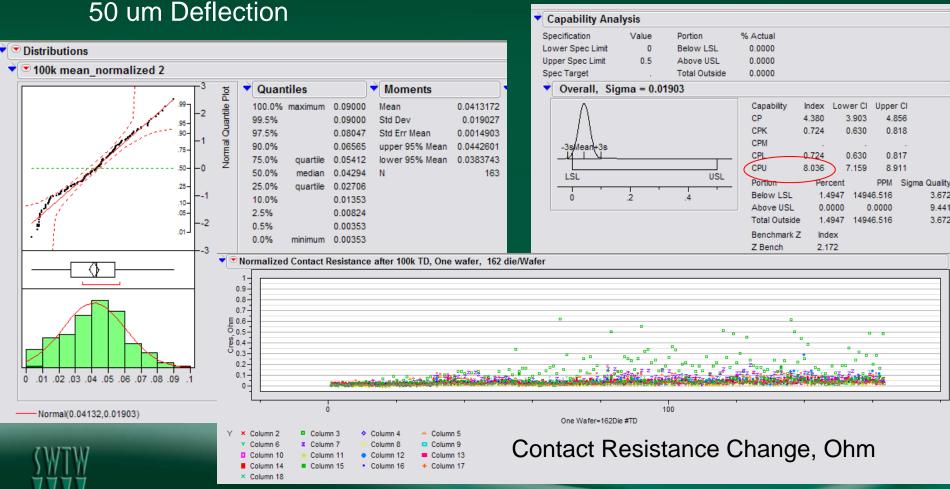




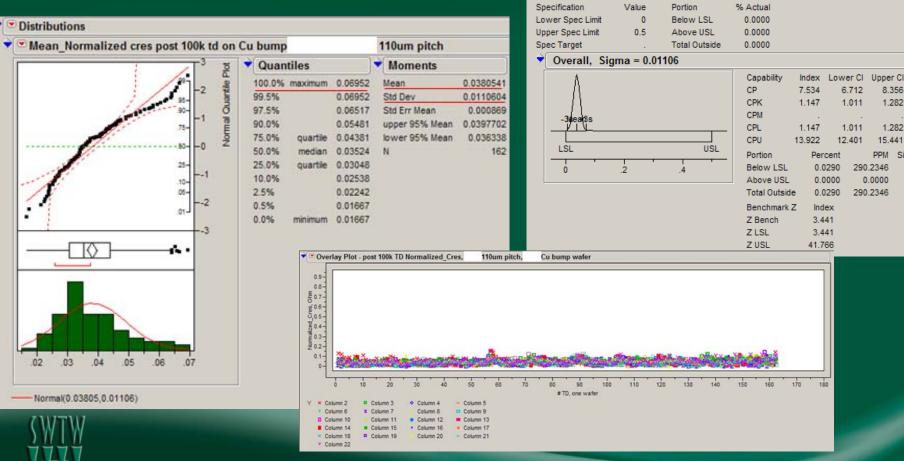




Post 100k Touch Down Performance on 130um pitch on Copper @



Post 100k Touch Down Performance on 110um pitch on Copper @
 50 um Deflection



Capability Analysis

9,441

4.941

- Contact Resistance Results on Copper
 - Cleaning performed prior to each wafer test

	CRES VALUE at INTERVAL, OHm							
	25k	50k	75k	100k				
Mean	0.0190	0.0231	0.0284	0.0410				
Std Dev	0.0046	0.0060	0.0162	0.0190				
99.5% Quantile	0.0388	0.0418	0.0841	0.0900				
100% Max	0.0388	0.0418	0.0841	0.0900				
CPU @ 0.5 USL	34.8000	26.4000	9.6000	8.0000				

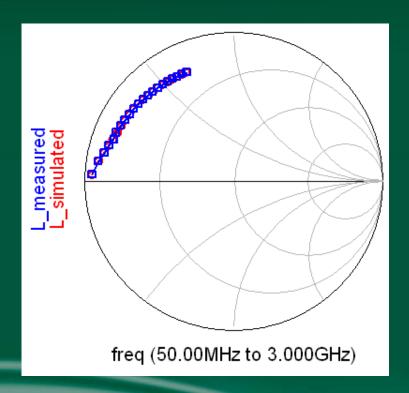
130um Pitch

	CRES VALUE at INTERVAL, OHm							
	25k	50k	75k	100k				
Mean	0.0390	0.0450	0.0410	0.0380				
Std Dev	0.0130	0.0150	0.0110	0.0110				
99.5% Quantile	0.0820	0.0780	0.0770	0.0700				
100% Max	0.0820	0.0780	0.0770	0.0700				
CPU @ 0.5 USL	12.0000	9.9000	14.4000	13.9000				

110um Pitch



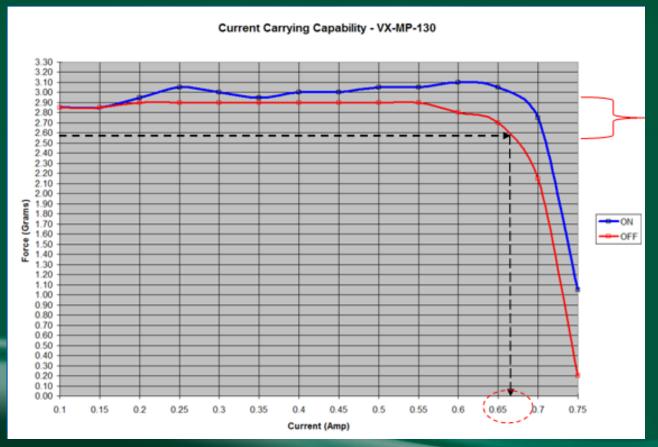
Effective Inductance



	VX-MP- 110	VX-MP- 130
PITCH (μm)	L (nH)	L(nH)
110	1.64	х
130	х	1.32
215	2.1	х
245	Х	1.92



CCC based on 10% CF Reduction under Steady State Current
 130 um Grid Array pitch Probe

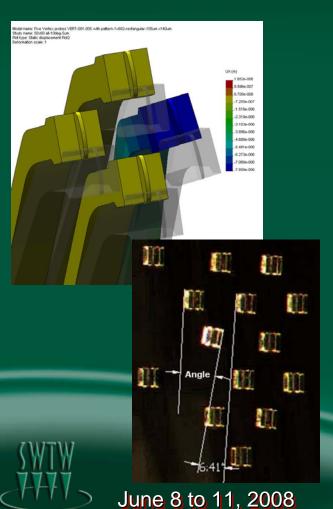


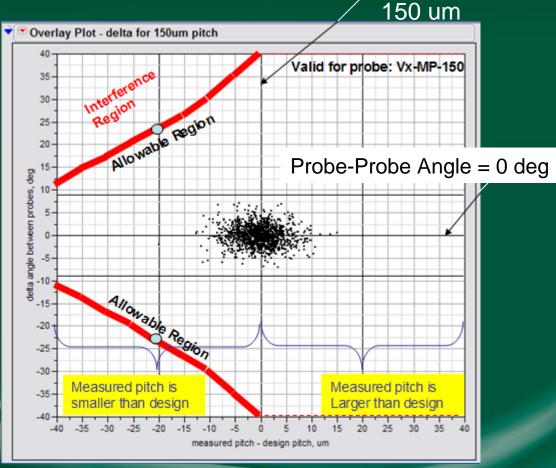
40um OT



Vx-MP Mechanical Performance

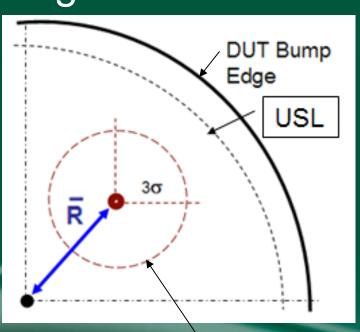
 Probe to Probe no-interference CPk = 3.6 @ 150 um pitch – for extreme bump height and scrub variation
 Nominal Pitch



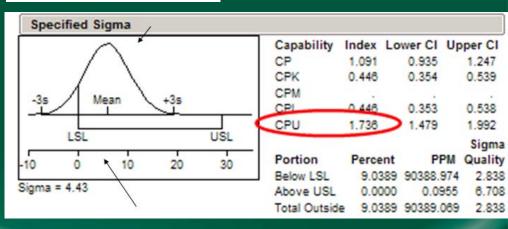


Vx-MP Tip-Bump Alignment Process Capability, CPU

 For 130um pitch & 90um nominal bump CPU= 1.74 Takes into account probe tip alignment and scrub motion



$$C_{p_{U}} = \frac{USL - \overline{R}}{3\sigma_{R}}$$

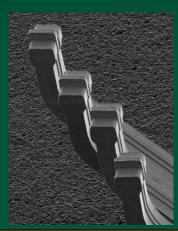


R=3*Stdev. Probe Tip location

Vx-MP Technology Pitch Capability Roadmap

Vx-MP





	Full Grid Array								Peripheral single & dual Row			
Pitch	150um	140um	130um	120	110um	100um	90um	80um	70um	60um	50um	40um
	V	√	√	√	√	V	•	•	V	V	٠	•
	√ = Available Capability											
	• = Under Development											



Summary/Next Steps

- Vx-MP technology platform combines accuracy of MEMS with flexibility of pre-made probes placed into customer specified x-y locations
- Addresses most aggressive wafer bump pitch roadmaps
- Tightly controlled scrub action optimizes electrical performance
- Next step: Larger footprint applications



Acknowledgements

- Miguel Enteria, R&D Manager, MicroProbe, Inc., Fremont, Ca
- Alex Shtarker, R&D, MicroProbe, Inc. Fremont, Ca
- Lich Tran, Sr. R&D Engineer, MicroProbe, Inc., Fremont, Ca

